



**ELECTROSTATIC SENSITIVE DEVICE**  
OBSERVE HANDLING PRECAUTIONS

**MITSUBISHI RF POWER MOS FET**

# RD06HHF1

**Silicon MOSFET Power Transistor 30MHz,6W**

## DESCRIPTION

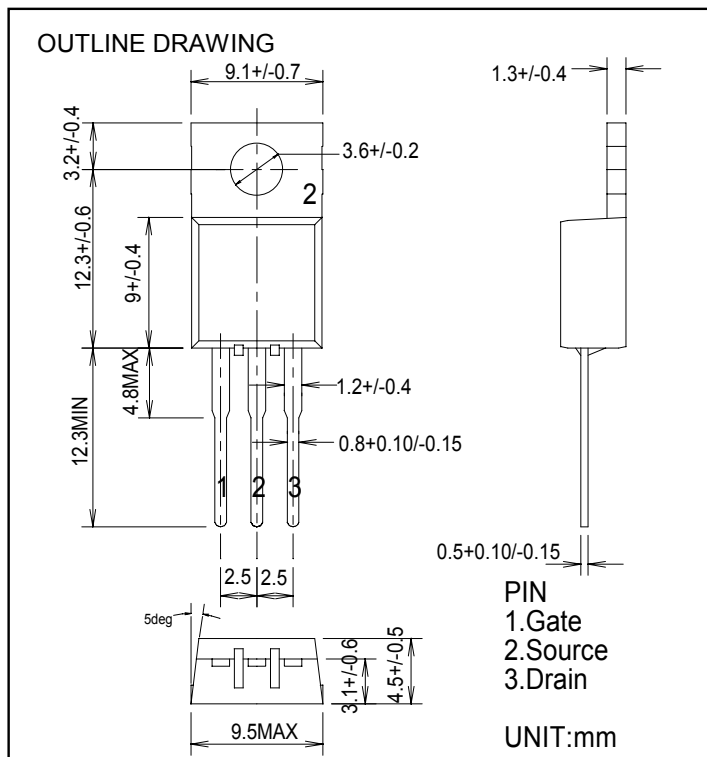
RD06HHF1 is a MOS FET type transistor specifically designed for HF RF power amplifiers applications.

## FEATURES

- High power gain:  
Pout>6W, Gp>16dB @Vdd=12.5V,f=30MHz

## APPLICATION

For output stage of high power amplifiers in HF band mobile radio sets.



## ABSOLUTE MAXIMUM RATINGS

(Tc=25°C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
Vdss	Drain to source voltage	Vgs=0V	50	V
Vgss	Gate to source voltage	Vds=0V	+/- 20	V
Pch	Channel dissipation	Tc=25°C	27.8	W
Pin	Input power	Zg=Zl=50Ω	0.3	W
ID	Drain current	-	3	A
Tch	Channel temperature	-	150	°C
Tstg	Storage temperature	-	-40 to +150	°C
Rth j-c	Thermal resistance	junction to case	4.5	°C/W

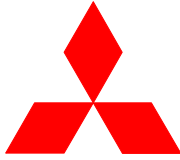
Note 1: Above parameters are guaranteed independently.

## ELECTRICAL CHARACTERISTICS

(Tc=25°C, UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX.	
IDSS	Zero gate voltage drain current	VDS=17V, VGS=0V	-	-	10	uA
IGSS	Gate to source leak current	VGS=10V, VDS=0V	-	-	1	uA
VTH	Gate threshold Voltage	VDS=12V, Ids=1mA	1.9	-	4.9	V
Pout	Output power	VDD=12.5V, Pin=0.15W, f=30MHz, Idq=0.5A	6	10	-	W
ηD	Drain efficiency	f=30MHz, Idq=0.5A	55	65	-	%
	Load VSWR tolerance	VDD=15.2V, Po=6W (Pin Control) f=30MHz, Idq=0.5A, Zg=50Ω Load VSWR=20:1 (All Phase)	No destroy			-

Note : Above parameters , ratings , limits and conditions are subject to change.



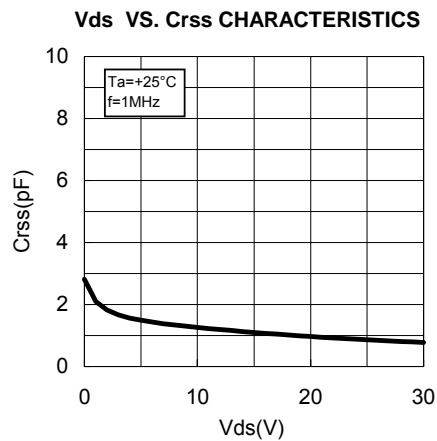
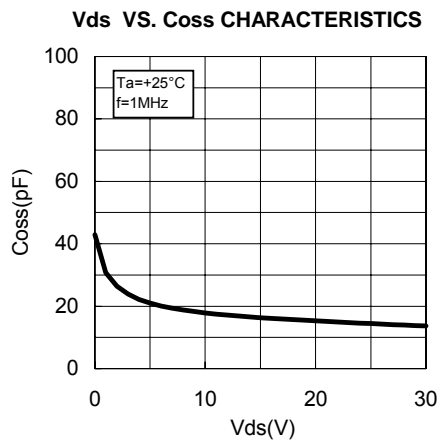
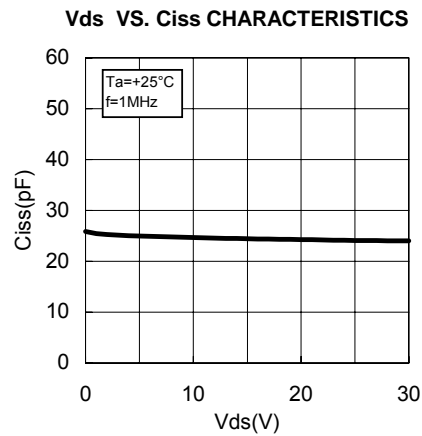
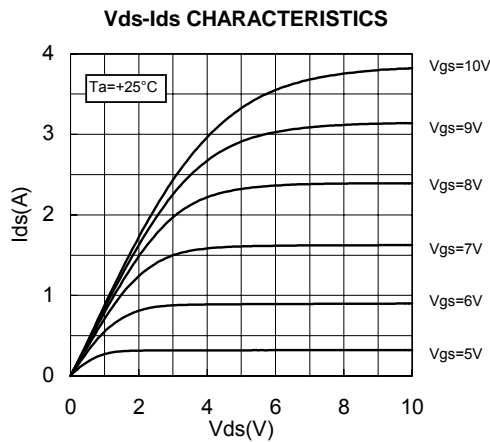
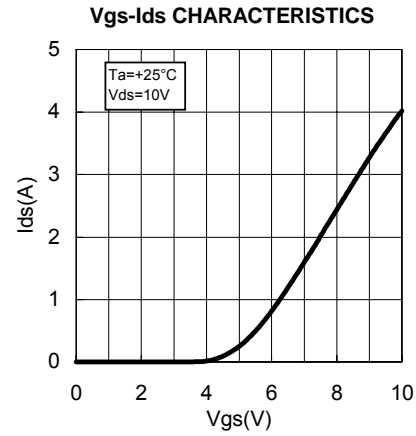
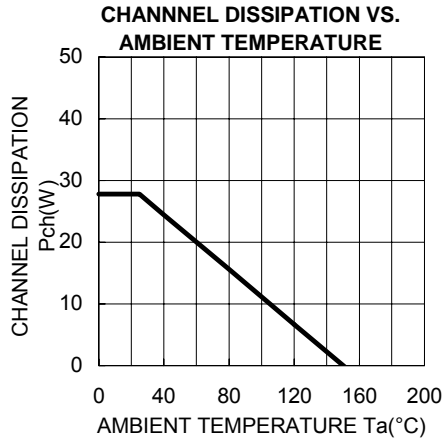
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## TYPICAL CHARACTERISTICS





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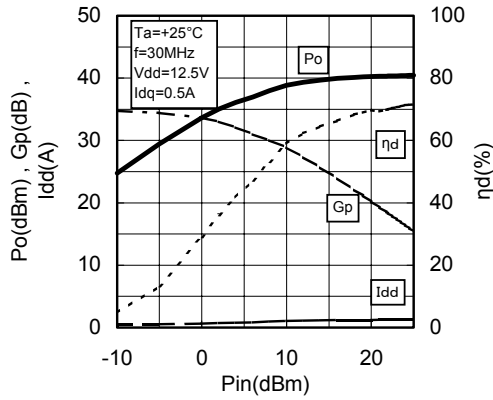
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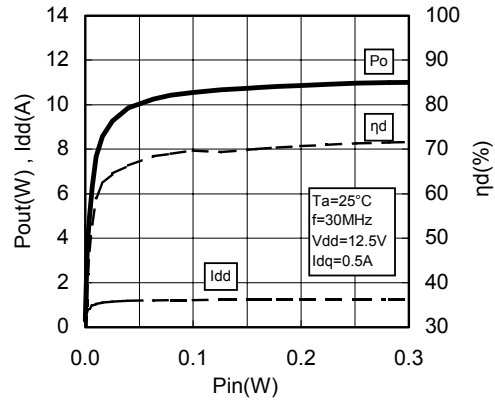
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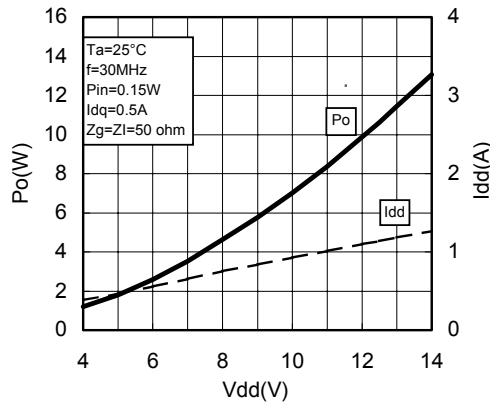
Pin-Po CHARACTERISTICS



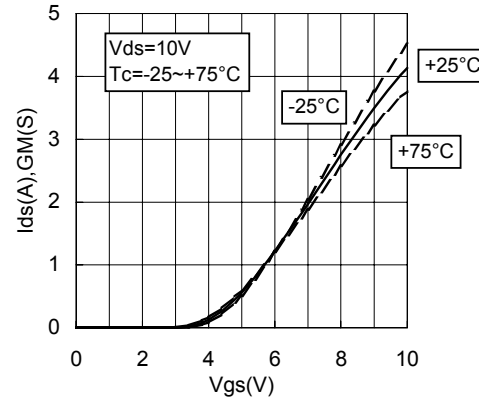
Pin-Po CHARACTERISTICS



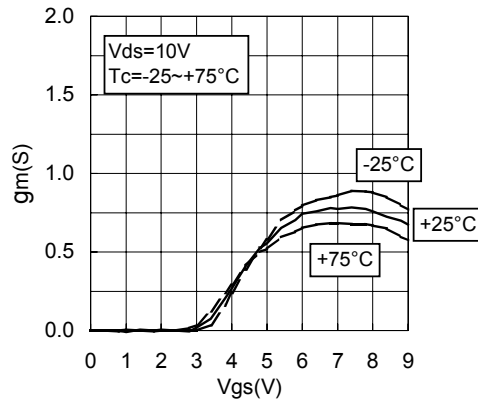
Vdd-Po CHARACTERISTICS



Vgs-Ids CHARACTERISTICS 2



Vgs-gm CHARACTERISTICS





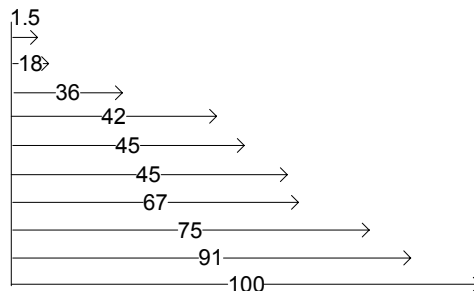
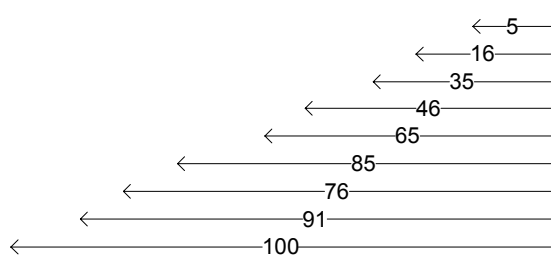
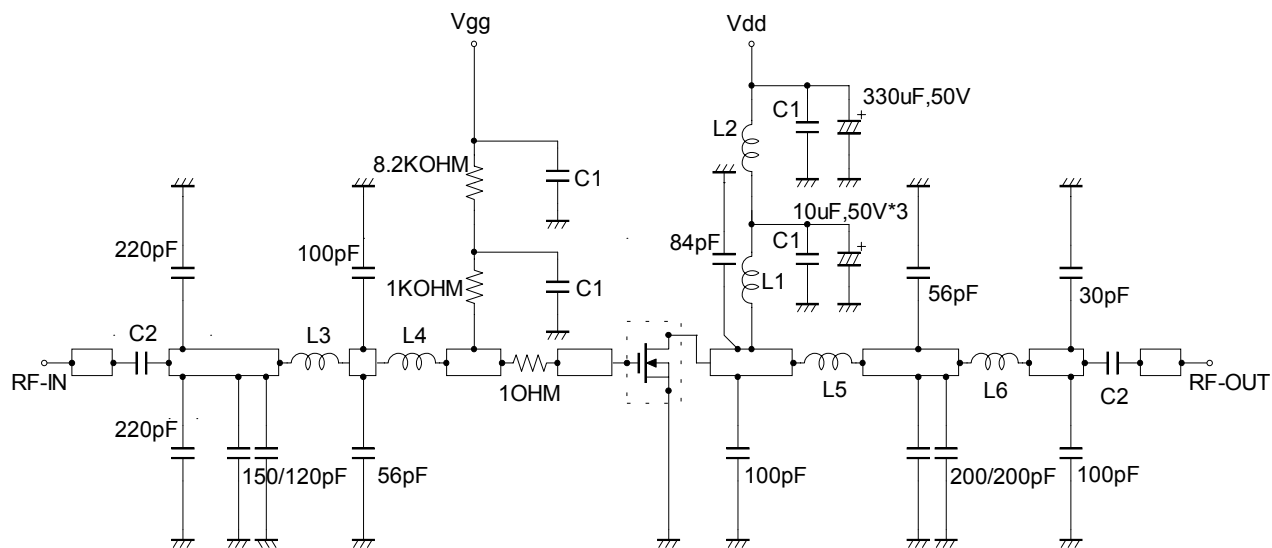
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## TEST CIRCUIT(f=30MHz)



C1:100pF,0.022uF,0.1uF in parallel  
C2:470uF\*2 in parallel

- L1:10Turns,I.D8mm,D0.9mm copper wire
- L2:10Turns,I.D6mm,D1.6mm silver plated copper wire
- L3:5Turns,I.D5.6mm,D0.9mm copper wire
- L4:6Turns,I.D5.6mm,D0.9mm copper wire
- L5:4Turns,I.D5.6mm,D0.9mm copper wire P=0.5mm
- L6:7Turns,I.D5.6mm,D0.9mm copper wire

Dimensions:mm  
Note:Board material- teflon substrate  
micro strip line width=4.2mm/50OHM,er:2.7,t=1.6mm



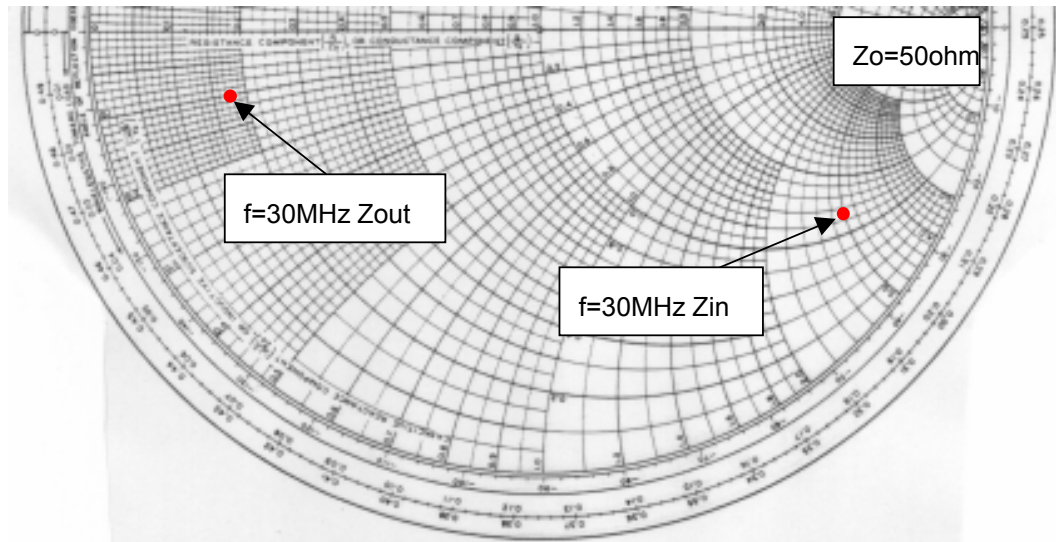
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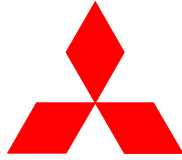
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## INPUT/OUTPUT IMPEDANCE VS.FREQUENCY CHARACTERISTICS



Zin , Zout

f	Zin	Zout	Conditions
(MHz)	(ohm)	(ohm)	
30	65.06-j150.9	8.75-j4.92	Po=10W, Vdd=12.5V,Pin=0.15W



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### RD06HHF1 S-PARAMETER DATA (@V<sub>dd</sub>=12.5V, I<sub>d</sub>=500mA)

Freq. [MHz]	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
10	0.985	-18.8	34.407	165.9	0.008	76.2	0.826	-17.3
30	0.900	-50.4	30.427	143.3	0.021	59.4	0.767	-43.6
50	0.799	-74.4	24.979	126.1	0.029	43.2	0.677	-65.0
100	0.667	-109.6	15.565	100.7	0.032	27.3	0.547	-96.8
150	0.636	-129.0	10.953	85.1	0.032	23.1	0.523	-113.4
200	0.630	-140.1	8.194	73.7	0.029	25.3	0.528	-124.7
250	0.645	-148.2	6.528	63.9	0.027	34.5	0.561	-132.7
300	0.663	-155.0	5.315	55.2	0.027	49.1	0.588	-139.6
350	0.685	-160.7	4.437	47.4	0.031	61.8	0.622	-145.9
400	0.708	-165.9	3.771	39.9	0.039	71.0	0.657	-151.7
450	0.729	-170.8	3.233	33.2	0.048	75.8	0.686	-157.0
500	0.752	-175.4	2.826	26.8	0.059	77.9	0.715	-162.3
550	0.771	-179.9	2.475	20.7	0.070	76.9	0.743	-167.6
600	0.789	-175.4	2.186	15.2	0.083	76.1	0.763	-172.3
650	0.804	-171.2	1.943	9.7	0.095	73.7	0.789	-177.3
700	0.819	-166.9	1.738	4.6	0.108	71.0	0.804	-178.1
750	0.834	-162.6	1.560	0.0	0.120	68.1	0.820	-173.5
800	0.842	-158.5	1.410	-4.5	0.133	65.0	0.837	-169.0
850	0.851	-154.3	1.275	-8.7	0.145	61.6	0.847	-164.8
900	0.859	-150.3	1.160	-12.6	0.157	58.2	0.858	-160.2
950	0.866	-146.2	1.058	-16.9	0.167	54.5	0.869	-155.7
1000	0.870	-142.3	0.963	-20.0	0.179	51.0	0.876	-151.8



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Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

**warning !**

Do not use the device at the exceeded the maximum rating condition. In case of plastic molded devices, the exceeded maximum rating condition may cause blowout, smoldering or catch fire of the molding resin due to extreme short current flow between the drain and the source of the device. These results causes in fire or injury.